



Form 1449 (Modified)  <b>Information Disclosure Statement By Applicant</b>  (Use Several Sheets if Necessary)	Atty Docket No. <b>UNTP025</b> Applicant: <b>RINERSON et al.</b> Filing Date <b>10/23/2003</b>	Application No.: <b>10/605,757</b>  Group <b>2818</b>
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#### U.S. Patent Documents

Examiner Initial	No.	Patent No.	Date	Patentee	Class	Sub-class	Filing Date
TH	A1	6,204,139	3/2001	Liu et al.			

#### Foreign Patent or Published Foreign Patent Application

Examiner Initial	No.	Document No.	Publication Date	Country or Patent Office	Class	Sub-class	Translation Yes	Translation No
	B1							

#### Other Documents

Examiner Initial	No.	Author, Title, Date, Place (e.g. Journal) of Publication
TH	C1	Beck et al., "Reproducible switching effect in thin oxide films for memory applications", 2000, Applied Physics Letters, Vol. 77, No. 1, pp. 139-141.
	C2	Betsuyaku et al., "Material Design for the Fabrication of <i>p</i> -type SrTiO <sub>3</sub> ", 2001, Jpn. J. Appl. Phys., Vol. 40, pp. 6911-6912.
	C3	Gerstner et al., "Nonvolatile memory effects in nitrogen doped tetrahedral amorphous carbon thin films", 1998, Journal of Applied Physics, Vol. 84, No. 10, pp. 5647-5651.
	C4	Kim et al., "Leakage Current Properties of (Ba, Sr)TiO <sub>3</sub> Films on Doped (Ba, Sr)RuO <sub>3</sub> Electrodes", 2002, Journal of the Korean Physical Society, Vol. 41, No. 2, pp. 227-231.
	C5	Liu et al., "Electric-pulse-induced reversible resistance change effect in magnetoresistive films", 2000, Applied Physics Letters, Vol. 76, No. 19, pp. 2749-2571.
	C6	Simmons et al., "New conduction and reversible memory phenomena in thin insulating films", 1967, Proc. Roy. Soc. A., Vol. 301, pp. 77-102.
	C7	Waser, "Bulk Conductivity and Defect Chemistry of Acceptor-Doped Strontium Titanate in the Quenched State", 1991, J. Am. Ceram. Soc., Vol. 74, No. 8, pp. 1934-1940.
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	C9	Watanabe et al., "Current-driven insulator-conductor transition and nonvolatile memory in chromium-doped SrTiO <sub>3</sub> single crystals", 2001, Applied Physics Letters, Vol. 78, No. 23, pp. 3738-3740.
	C10	Watanabe, "Electrical transport through Pb(Zr, Ti)O <sub>3</sub> <i>p-n</i> and <i>p-p</i> heterostructures modulated by bound charges at a ferroelectric surface: Ferroelectric <i>p-n</i> diode",
	C11	Watanabe et al., "Highly Resolved Conduction Properties of Ferroelectric/Semiconductor Diodes Exhibiting Memory Effect", 1998, Journal of the Korean Physical Society, Vol. 32, pp. S1361-S1364.
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	Date Considered	Jan. 2005

Examiner: Initial citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.